

/ Descriptions

SOT-23 PNP Silicon PNP transistor in a SOT-23 Plastic Package.

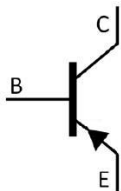
/ Features

High voltage, low saturation voltage, low collector output capacitance, complementary pair with MMBTA42.

/ Applications

High voltage control circuit.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Emitter PIN 3 Collector

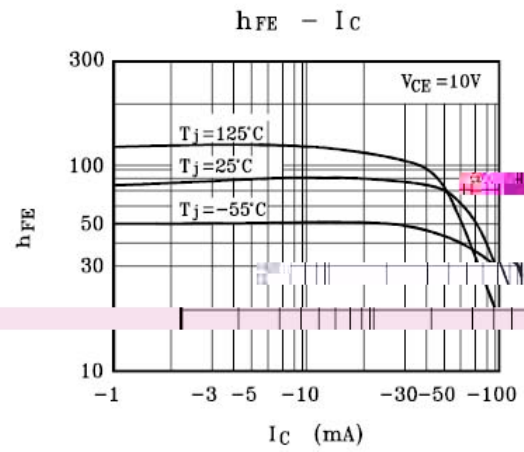
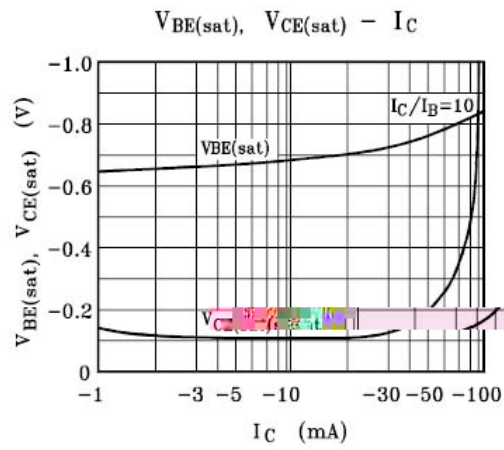
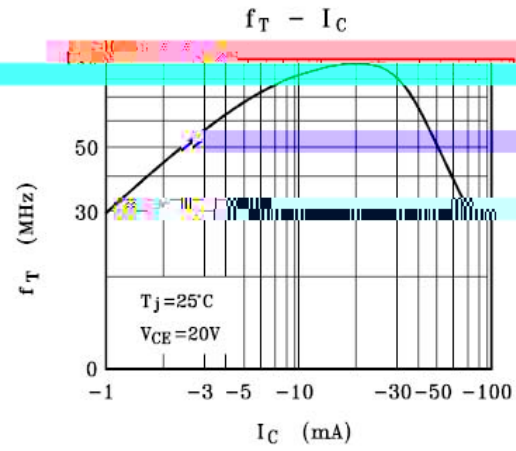
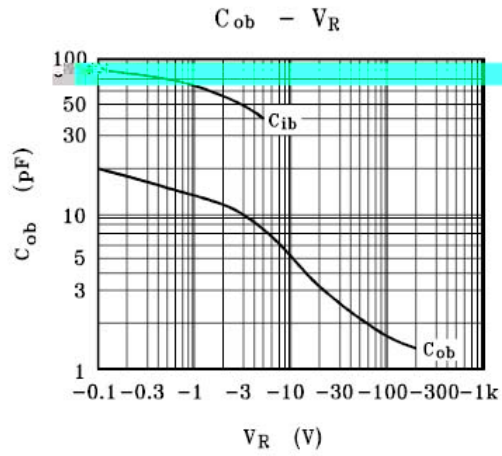
/ Marking

h_{FE} Range	>40
Marking	H2D

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-300	V
Collector to Emitter Voltage	V_{CEO}	-300	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-500	mA
Collector Power Dissipation	P_C	350	mW
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -100\mu A$ $I_E = 0$	-300			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -1.0mA$ $I_B = 0$	-300			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E = -100\mu A$ $I_C = 0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -200V$ $I_E = 0$				

/ Electrical Characteristic Curve



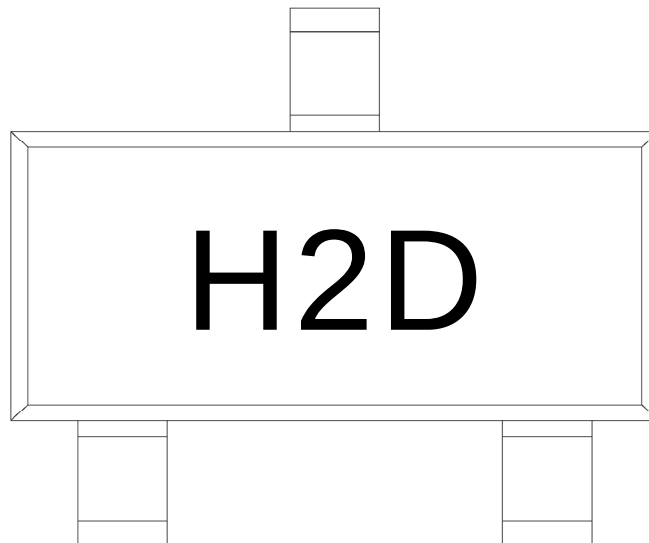
/ Package Dimensions

SOT-23

单位: mm



/ Marking Instructions



H

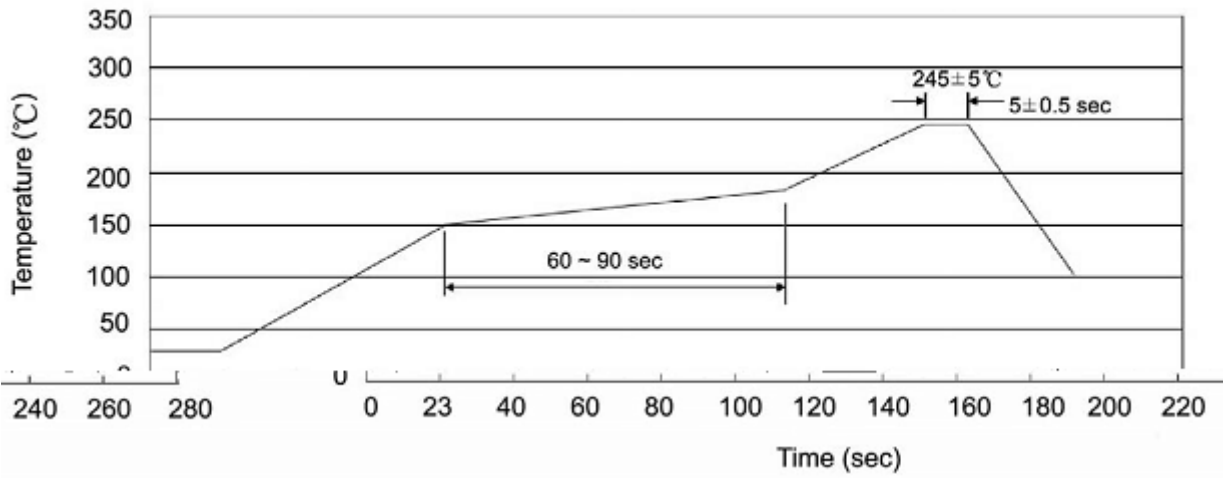
2D

Note:

H: Company Code.

2D: Product Type Code.

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Note:

- | | | | | | |
|---|----|-------|----|-----------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | | 245±5 | | 5±0.5sec; | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 | | | 2 | 10 /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

260±5	10±1 sec.	Temp.:260±5	Time:10±1 sec
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/ Packaging SPEC.

/ REEL

Package Type	Units
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